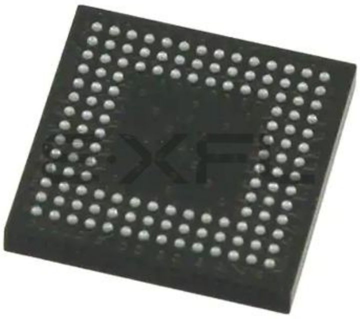
Lattice Semiconductor Corporation - LCMXO2-256ZE-3MG132I Datasheet



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Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications,

Details	
Product Status	Active
Number of LABs/CLBs	32
Number of Logic Elements/Cells	256
Total RAM Bits	-
Number of I/O	55
Number of Gates	-
Voltage - Supply	1.14V ~ 1.26V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	132-LFBGA, CSPBGA
Supplier Device Package	132-CSPBGA (8x8)
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/lcmxo2-256ze-3mg132i

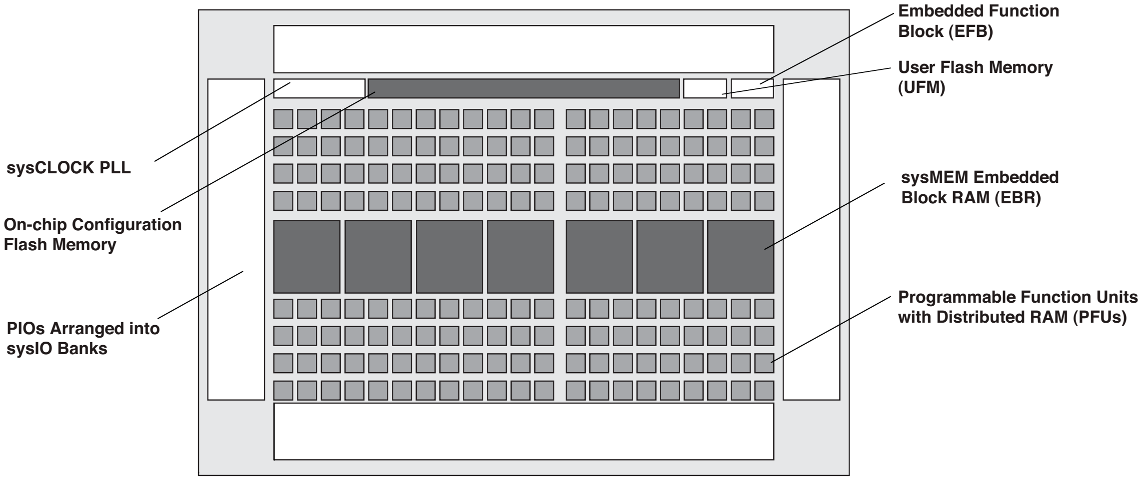
MachXO2 Family Data Sheet Architecture

March 2016 **Data Sheet DS1035**

Architecture Overview

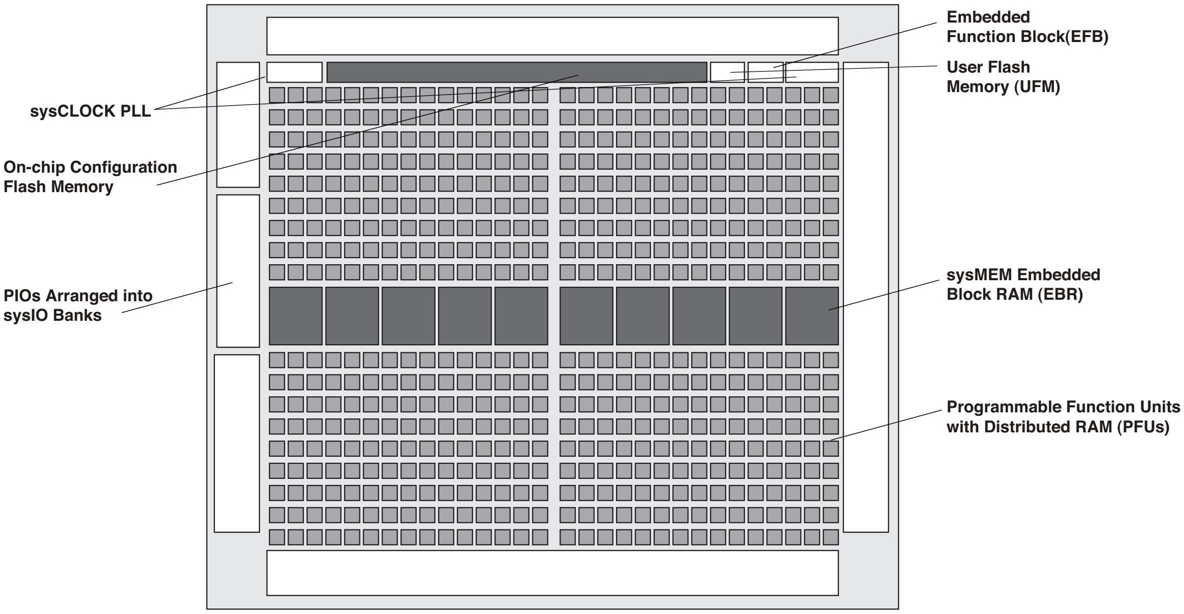
The MachXO2 family architecture contains an array of logic blocks surrounded by Programmable I/O (PIO). The larger logic density devices in this family have sysCLOCK™ PLLs and blocks of sysMEM Embedded Block RAM (EBRs). Figure 2-1 and Figure 2-2 show the block diagrams of the various family members.

Figure 2-1. Top View of the MachXO2-1200 Device



Note: MachXO2-256, and MachXO2-640/U are similar to MachXO2-1200. MachXO2-256 has a lower LUT count and no PLL or EBR blocks. MachXO2-640 has no PLL, a lower LUT count and two EBR blocks. MachXO2-640U has a lower LUT count, one PLL and seven EBR blocks.

Figure 2-2. Top View of the MachXO2-4000 Device



Note: MachXO2-1200U, MachXO2-2000/U and MachXO2-7000 are similar to MachXO2-4000. MachXO2-1200U and MachXO2-2000 have a lower LUT count, one PLL, and eight EBR blocks. MachXO2-2000U has a lower LUT count, two PLLs, and 10 EBR blocks. MachXO2-7000 has a higher LUT count, two PLLs, and 26 EBR blocks.

This phase shift can be either programmed during configuration or can be adjusted dynamically. In dynamic mode, the PLL may lose lock after a phase adjustment on the output used as the feedback source and not relock until the t_{LOCK} parameter has been satisfied.

The MachXO2 also has a feature that allows the user to select between two different reference clock sources dynamically. This feature is implemented using the PLLREFCS primitive. The timing parameters for the PLL are shown in the sysCLOCK PLL Timing table.

The MachXO2 PLL contains a WISHBONE port feature that allows the PLL settings, including divider values, to be dynamically changed from the user logic. When using this feature the EFB block must also be instantiated in the design to allow access to the WISHBONE ports. Similar to the dynamic phase adjustment, when PLL settings are updated through the WISHBONE port the PLL may lose lock and not relock until the t_{LOCK} parameter has been satisfied. The timing parameters for the PLL are shown in the sysCLOCK PLL Timing table.

For more details on the PLL and the WISHBONE interface, see TN1199, MachXO2 sysCLOCK PLL Design and Usage Guide.

Figure 2-7. PLL Diagram

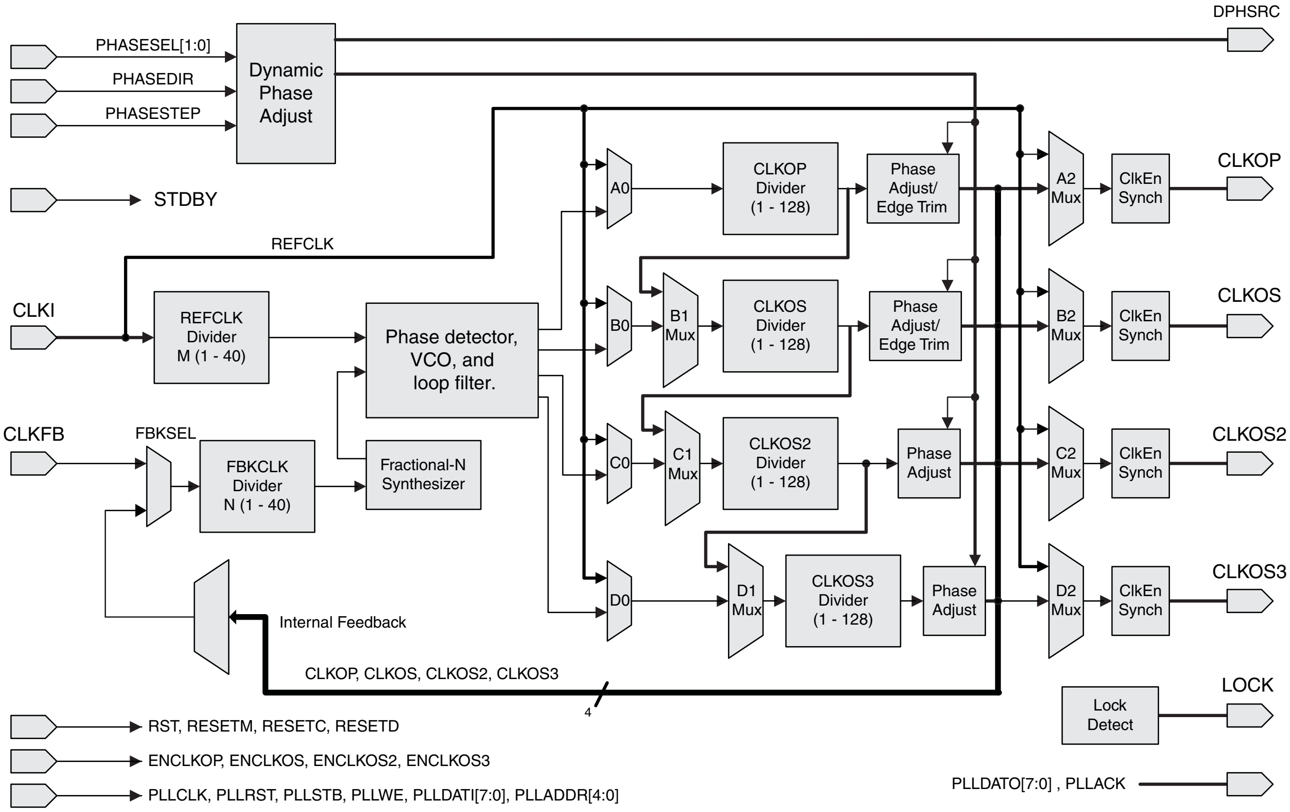


Table 2-4 provides signal descriptions of the PLL block.

Table 2-4. PLL Signal Descriptions

Port Name	I/O	Description
CLKI	I	Input clock to PLL
CLKFB	I	Feedback clock
PHASESEL[1:0]	I	Select which output is affected by Dynamic Phase adjustment ports
PHASEDIR	I	Dynamic Phase adjustment direction
PHASESTEP	I	Dynamic Phase step – toggle shifts VCO phase adjust by one step.

Table 2-5. sysMEM Block Configurations

Memory Mode	Configurations
Single Port	8,192 x 1 4,096 x 2 2,048 x 4 1,024 x 9
True Dual Port	8,192 x 1 4,096 x 2 2,048 x 4 1,024 x 9
Pseudo Dual Port	8,192 x 1 4,096 x 2 2,048 x 4 1,024 x 9 512 x 18
FIFO	8,192 x 1 4,096 x 2 2,048 x 4 1,024 x 9 512 x 18

Bus Size Matching

All of the multi-port memory modes support different widths on each of the ports. The RAM bits are mapped LSB word 0 to MSB word 0, LSB word 1 to MSB word 1, and so on. Although the word size and number of words for each port varies, this mapping scheme applies to each port.

RAM Initialization and ROM Operation

If desired, the contents of the RAM can be pre-loaded during device configuration. EBR initialization data can be loaded from the UFM. To maximize the number of UFM bits, initialize the EBRs used in your design to an all-zero pattern. Initializing to an all-zero pattern does not use up UFM bits. MachXO2 devices have been designed such that multiple EBRs share the same initialization memory space if they are initialized to the same pattern.

By preloading the RAM block during the chip configuration cycle and disabling the write controls, the sysMEM block can also be utilized as a ROM.

Memory Cascading

Larger and deeper blocks of RAM can be created using EBR sysMEM Blocks. Typically, the Lattice design tools cascade memory transparently, based on specific design inputs.

Single, Dual, Pseudo-Dual Port and FIFO Modes

Figure 2-8 shows the five basic memory configurations and their input/output names. In all the sysMEM RAM modes, the input data and addresses for the ports are registered at the input of the memory array. The output data of the memory is optionally registered at the memory array output.

The EBR memory supports three forms of write behavior for single or dual port operation:

1. **Normal** – Data on the output appears only during the read cycle. During a write cycle, the data (at the current address) does not appear on the output. This mode is supported for all data widths.
2. **Write Through** – A copy of the input data appears at the output of the same port. This mode is supported for all data widths.
3. **Read-Before-Write** – When new data is being written, the old contents of the address appears at the output.

FIFO Configuration

The FIFO has a write port with data-in, CEW, WE and CLKW signals. There is a separate read port with data-out, RCE, RE and CLKR signals. The FIFO internally generates Almost Full, Full, Almost Empty and Empty Flags. The Full and Almost Full flags are registered with CLKW. The Empty and Almost Empty flags are registered with CLKR. Table 2-7 shows the range of programming values for these flags.

Table 2-7. Programmable FIFO Flag Ranges

Flag Name	Programming Range
Full (FF)	1 to max (up to 2^N-1)
Almost Full (AF)	1 to Full-1
Almost Empty (AE)	1 to Full-1
Empty (EF)	0

N = Address bit width.

The FIFO state machine supports two types of reset signals: RST and RPRST. The RST signal is a global reset that clears the contents of the FIFO by resetting the read/write pointer and puts the FIFO flags in their initial reset state. The RPRST signal is used to reset the read pointer. The purpose of this reset is to retransmit the data that is in the FIFO. In these applications it is important to keep careful track of when a packet is written into or read from the FIFO.

Memory Core Reset

The memory core contains data output latches for ports A and B. These are simple latches that can be reset synchronously or asynchronously. RSTA and RSTB are local signals, which reset the output latches associated with port A and port B respectively. The Global Reset (GSRN) signal resets both ports. The output data latches and associated resets for both ports are as shown in Figure 2-9.

PIO

The PIO contains three blocks: an input register block, output register block and tri-state register block. These blocks contain registers for operating in a variety of modes along with the necessary clock and selection logic.

Table 2-8. PIO Signal List

Pin Name	I/O Type	Description
CE	Input	Clock Enable
D	Input	Pin input from sysIO buffer.
INDD	Output	Register bypassed input.
INCK	Output	Clock input
Q0	Output	DDR positive edge input
Q1	Output	Registered input/DDR negative edge input
D0	Input	Output signal from the core (SDR and DDR)
D1	Input	Output signal from the core (DDR)
TD	Input	Tri-state signal from the core
Q	Output	Data output signals to sysIO Buffer
TQ	Output	Tri-state output signals to sysIO Buffer
DQSR90[1]	Input	DQS shift 90-degree read clock
DQSW90[1]	Input	DQS shift 90-degree write clock
DDRCLKPOL[1]	Input	DDR input register polarity control signal from DQS
SCLK	Input	System clock for input and output/tri-state blocks.
RST	Input	Local set reset signal

1. Available in PIO on right edge only.

Input Register Block

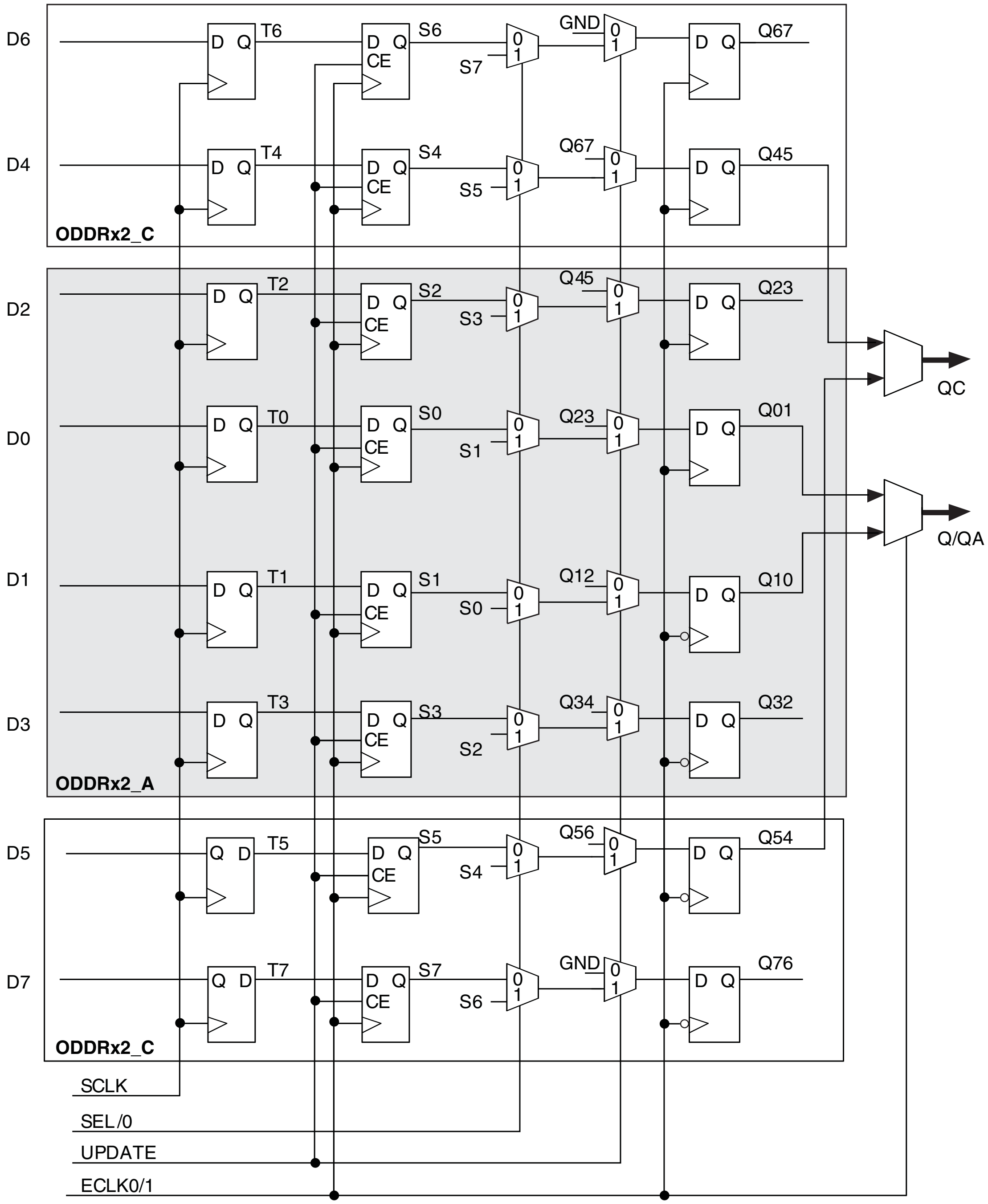
The input register blocks for the PIOs on all edges contain delay elements and registers that can be used to condition high-speed interface signals before they are passed to the device core. In addition to this functionality, the input register blocks for the PIOs on the right edge include built-in logic to interface to DDR memory.

Figure 2-12 shows the input register block for the PIOs located on the left, top and bottom edges. Figure 2-13 shows the input register block for the PIOs on the right edge.

Left, Top, Bottom Edges

Input signals are fed from the sysIO buffer to the input register block (as signal D). If desired, the input signal can bypass the register and delay elements and be used directly as a combinatorial signal (INDD), and a clock (INCK). If an input delay is desired, users can select a fixed delay. I/Os on the bottom edge also have a dynamic delay, DEL[4:0]. The delay, if selected, reduces input register hold time requirements when using a global clock. The input block allows two modes of operation. In single data rate (SDR) the data is registered with the system clock (SCLK) by one of the registers in the single data rate sync register block. In Generic DDR mode, two registers are used to sample the data on the positive and negative edges of the system clock (SCLK) signal, creating two data streams.

Figure 2-17. Output Gearbox



More information on the output gearbox is available in TN1203, Implementing High-Speed Interfaces with MachXO2 Devices.

MachXO2-640U, MachXO2-1200/U, MachXO2-2000/U, MachXO2-4000 and MachXO2-7000 devices contain three types of sysIO buffer pairs.

1. **Left and Right sysIO Buffer Pairs**
   The sysIO buffer pairs in the left and right banks of the device consist of two single-ended output drivers and two single-ended input buffers (for ratioed inputs such as LVCMOS and LVTTL). The I/O pairs on the left and right of the devices also have differential and referenced input buffers.

2. **Bottom sysIO Buffer Pairs**
   The sysIO buffer pairs in the bottom bank of the device consist of two single-ended output drivers and two single-ended input buffers (for ratioed inputs such as LVCMOS and LVTTL). The I/O pairs on the bottom also have differential and referenced input buffers. Only the I/Os on the bottom banks have programmable PCI clamps and differential input termination. The PCI clamp is enabled after V_{CC} and V_{CCIO} are at valid operating levels and the device has been configured.

3. **Top sysIO Buffer Pairs**
   The sysIO buffer pairs in the top bank of the device consist of two single-ended output drivers and two single-ended input buffers (for ratioed inputs such as LVCMOS and LVTTL). The I/O pairs on the top also have differential and referenced I/O buffers. Half of the sysIO buffer pairs on the top edge have true differential outputs. The sysIO buffer pair comprising of the A and B PIOs in every PIC on the top edge have a differential output driver. The referenced input buffer can also be configured as a differential input buffer.

Typical I/O Behavior During Power-up

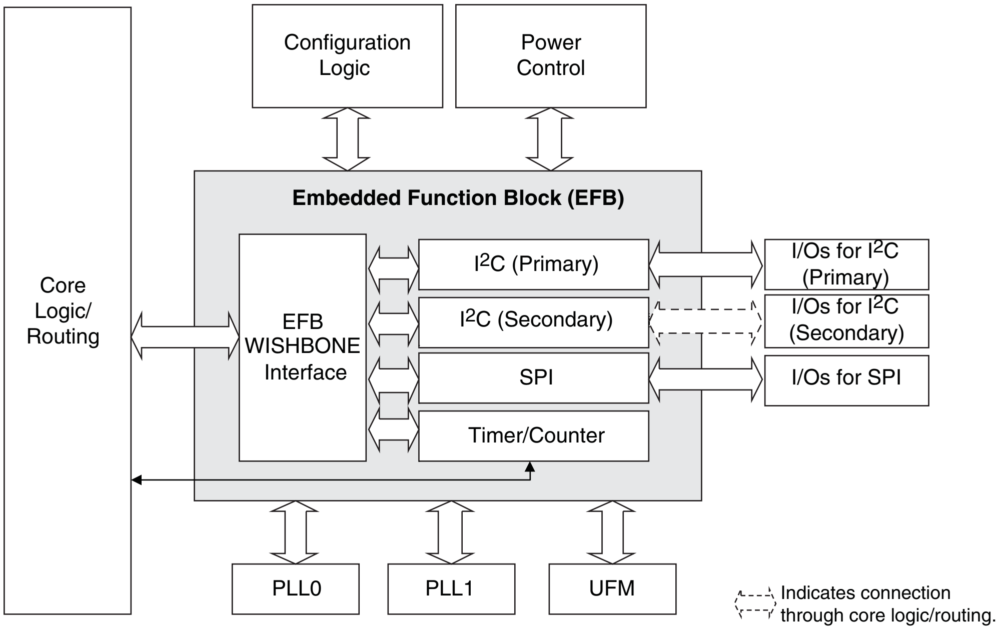
The internal power-on-reset (POR) signal is deactivated when V_{CC} and V_{CCIO0} have reached V_{PORUP} level defined in the Power-On-Reset Voltage table in the DC and Switching Characteristics section of this data sheet. After the POR signal is deactivated, the FPGA core logic becomes active. It is the user's responsibility to ensure that all V_{CCIO} banks are active with valid input logic levels to properly control the output logic states of all the I/O banks that are critical to the application. The default configuration of the I/O pins in a blank device is tri-state with a weak pull-down to GND (some pins such as PROGRAMN and the JTAG pins have weak pull-up to V_{CCIO} as the default functionality). The I/O pins will maintain the blank configuration until V_{CC} and V_{CCIO} (for I/O banks containing configuration I/Os) have reached V_{PORUP} levels at which time the I/Os will take on the user-configured settings only after a proper download/configuration.

Supported Standards

The MachXO2 sysIO buffer supports both single-ended and differential standards. Single-ended standards can be further subdivided into LVCMOS, LVTTL, and PCI. The buffer supports the LVTTL, PCI, LVCMOS 1.2, 1.5, 1.8, 2.5, and 3.3 V standards. In the LVCMOS and LVTTL modes, the buffer has individually configurable options for drive strength, bus maintenance (weak pull-up, weak pull-down, bus-keeper latch or none) and open drain. BLVDS, MLVDS and LVPECL output emulation is supported on all devices. The MachXO2-640U, MachXO2-1200/U and higher devices support on-chip LVDS output buffers on approximately 50% of the I/Os on the top bank. Differential receivers for LVDS, BLVDS, MLVDS and LVPECL are supported on all banks of MachXO2 devices. PCI support is provided in the bottom bank of theMachXO2-640U, MachXO2-1200/U and higher density devices. Table 2-11 summarizes the I/O characteristics of the MachXO2 PLDs.

Tables 2-11 and 2-12 show the I/O standards (together with their supply and reference voltages) supported by the MachXO2 devices. For further information on utilizing the sysIO buffer to support a variety of standards please see TN1202, MachXO2 sysIO Usage Guide.

Figure 2-20. Embedded Function Block Interface



Hardened I²C IP Core

Every MachXO2 device contains two I²C IP cores. These are the primary and secondary I²C IP cores. Either of the two cores can be configured either as an I²C master or as an I²C slave. The only difference between the two IP cores is that the primary core has pre-assigned I/O pins whereas users can assign I/O pins for the secondary core.

When the IP core is configured as a master it will be able to control other devices on the I²C bus through the interface. When the core is configured as the slave, the device will be able to provide I/O expansion to an I²C Master. The I²C cores support the following functionality:

- Master and Slave operation
- 7-bit and 10-bit addressing
- Multi-master arbitration support
- Up to 400 kHz data transfer speed
- General call support
- Interface to custom logic through 8-bit WISHBONE interface

For more details on these embedded functions, please refer to TN1205, Using User Flash Memory and Hardened Control Functions in MachXO2 Devices.

User Flash Memory (UFM)

MachXO2-640/U and higher density devices provide a User Flash Memory block, which can be used for a variety of applications including storing a portion of the configuration image, initializing EBRs, to store PROM data or, as a general purpose user Flash memory. The UFM block connects to the device core through the embedded function block WISHBONE interface. Users can also access the UFM block through the JTAG, I^2C and SPI interfaces of the device. The UFM block offers the following features:

- Non-volatile storage up to 256 kbits
- 100K write cycles
- Write access is performed page-wise; each page has 128 bits (16 bytes)
- Auto-increment addressing
- WISHBONE interface

For more information on the UFM, please refer to TN1205, Using User Flash Memory and Hardened Control Functions in MachXO2 Devices.

Standby Mode and Power Saving Options

MachXO2 devices are available in three options for maximum flexibility: ZE, HC and HE devices. The ZE devices have ultra low static and dynamic power consumption. These devices use a 1.2 V core voltage that further reduces power consumption. The HC and HE devices are designed to provide high performance. The HC devices have a built-in voltage regulator to allow for 2.5 V V_{CC} and 3.3 V V_{CC} while the HE devices operate at 1.2 V V_{CC}.

MachXO2 devices have been designed with features that allow users to meet the static and dynamic power requirements of their applications by controlling various device subsystems such as the bandgap, power-on-reset circuitry, I/O bank controllers, power guard, on-chip oscillator, PLLs, etc. In order to maximize power savings, MachXO2 devices support an ultra low power Stand-by mode. While most of these features are available in all three device types, these features are mainly intended for use with MachXO2 ZE devices to manage power consumption.

In the stand-by mode the MachXO2 devices are powered on and configured. Internal logic, I/Os and memories are switched on and remain operational, as the user logic waits for an external input. The device enters this mode when the standby input of the standby controller is toggled or when an appropriate I^2C or JTAG instruction is issued by an external master. Various subsystems in the device such as the band gap, power-on-reset circuitry etc can be configured such that they are automatically turned “off” or go into a low power consumption state to save power when the device enters this state. Note that the MachXO2 devices are powered on when in standby mode and all power supplies should remain in the Recommended Operating Conditions.

Table 2-18. MachXO2 Power Saving Features Description

Device Subsystem	Feature Description
Bandgap	The bandgap can be turned off in standby mode. When the Bandgap is turned off, analog circuitry such as the POR, PLLs, on-chip oscillator, and referenced and differential I/O buffers are also turned off. Bandgap can only be turned off for 1.2 V devices.
Power-On-Reset (POR)	The POR can be turned off in standby mode. This monitors VCC levels. In the event of unsafe V_{CC} drops, this circuit reconfigures the device. When the POR circuitry is turned off, limited power detector circuitry is still active. This option is only recommended for applications in which the power supply rails are reliable.
On-Chip Oscillator	The on-chip oscillator has two power saving features. It may be switched off if it is not needed in your design. It can also be turned off in Standby mode.
PLL	Similar to the on-chip oscillator, the PLL also has two power saving features. It can be statically switched off if it is not needed in a design. It can also be turned off in Standby mode. The PLL will wait until all output clocks from the PLL are driven low before powering off.
I/O Bank Controller	Referenced and differential I/O buffers (used to implement standards such as HSTL, SSTL and LVDS) consume more than ratioed single-ended I/Os such as LVCMOS and LVTTL. The I/O bank controller allows the user to turn these I/Os off dynamically on a per bank selection.
Dynamic Clock Enable for Primary Clock Nets	Each primary clock net can be dynamically disabled to save power.
Power Guard	Power Guard is a feature implemented in input buffers. This feature allows users to switch off the input buffer when it is not needed. This feature can be used in both clock and data paths. Its biggest impact is that in the standby mode it can be used to switch off clock inputs that are distributed using general routing resources.

For more details on the standby mode refer to TN1198, Power Estimation and Management for MachXO2 Devices.

Power On Reset

MachXO2 devices have power-on reset circuitry to monitor V_{CCINT} and V_{CCIO} voltage levels during power-up and operation. At power-up, the POR circuitry monitors V_{CCINT} and V_{CCIO0} (controls configuration) voltage levels. It then triggers download from the on-chip configuration Flash memory after reaching the V_{PORUP} level specified in the Power-On-Reset Voltage table in the DC and Switching Characteristics section of this data sheet. For devices without voltage regulators (ZE and HE devices), V_{CCINT} is the same as the V_{CC} supply voltage. For devices with voltage regulators (HC devices), V_{CCINT} is regulated from the V_{CC} supply voltage. From this voltage reference, the time taken for configuration and entry into user mode is specified as Flash Download Time ($t_{REFRESH}$) in the DC and Switching Characteristics section of this data sheet. Before and during configuration, the I/Os are held in tri-state. I/Os are released to user functionality once the device has finished configuration. Note that for HC devices, a separate POR circuit monitors external V_{CC} voltage in addition to the POR circuit that monitors the internal post-regulated power supply voltage level.

Once the device enters into user mode, the POR circuitry can optionally continue to monitor V_{CCINT} levels. If V_{CCINT} drops below $V_{PORDNBG}$ level (with the bandgap circuitry switched on) or below $V_{PORDNSRAM}$ level (with the bandgap circuitry switched off to conserve power) device functionality cannot be guaranteed. In such a situation the POR issues a reset and begins monitoring the V_{CCINT} and V_{CCIO} voltage levels. $V_{PORDNBG}$ and $V_{PORDNSRAM}$ are both specified in the Power-On-Reset Voltage table in the DC and Switching Characteristics section of this data sheet.

Note that once a ZE or HE device enters user mode, users can switch off the bandgap to conserve power. When the bandgap circuitry is switched off, the POR circuitry also shuts down. The device is designed such that a minimal, low power POR circuit is still operational (this corresponds to the $V_{PORDNSRAM}$ reset point described in the paragraph above). However this circuit is not as accurate as the one that operates when the bandgap is switched on. The low power POR circuit emulates an SRAM cell and is biased to trip before the vast majority of SRAM cells flip. If users are concerned about the V_{CC} supply dropping below V_{CC} (min) they should not shut down the bandgap or POR circuit.

DC Electrical Characteristics

Over Recommended Operating Conditions

Symbol	Parameter	Condition	Min.	Typ.	Max.	Units
I_{IL}, I_{IH}[1, 4]	Input or I/O Leakage	Clamp OFF and $V_{CCIO} < V_{IN} < V_{IH}$ (MAX)	—	—	+175	µA
		Clamp OFF and $V_{IN} = V_{CCIO}$	–10	—	10	µA
		Clamp OFF and V_{CCIO} –0.97 V < V_{IN} < V_{CCIO}	–175	—	—	µA
		Clamp OFF and 0 V < V_{IN} < V_{CCIO} –0.97 V	—	—	10	µA
		Clamp OFF and V_{IN} = GND	—	—	10	µA
		Clamp ON and 0 V < V_{IN} < V_{CCIO}	—	—	10	µA
I_{PU}	I/O Active Pull-up Current	0 < V_{IN} < 0.7 V_{CCIO}	–30	—	-309	µA
I_{PD}	I/O Active Pull-down Current	V_{IL} (MAX) < V_{IN} < V_{CCIO}	30	—	305	µA
I_{BHLS}	Bus Hold Low sustaining current	$V_{IN} = V_{IL}$ (MAX)	30	—	—	µA
I_{BHHS}	Bus Hold High sustaining current	$V_{IN} = 0.7V_{CCIO}$	–30	—	—	µA
I_{BHLO}	Bus Hold Low Overdrive current	$0 \le V_{IN} \le V_{CCIO}$	—	—	305	µA
I_{BHHO}	Bus Hold High Overdrive current	$0 \le V_{IN} \le V_{CCIO}$	—	—	–309	µA
V_{BHT}[3]	Bus Hold Trip Points		V_{IL} (MAX)	—	V_{IH} (MIN)	V
C1	I/O Capacitance[2]	V_{CCIO} = 3.3 V, 2.5 V, 1.8 V, 1.5 V, 1.2 V, V_{CC} = Typ., V_{IO} = 0 to V_{IH} (MAX)	3	5	9	pF
C2	Dedicated Input Capacitance[2]	V_{CCIO} = 3.3 V, 2.5 V, 1.8 V, 1.5 V, 1.2 V, V_{CC} = Typ., V_{IO} = 0 to V_{IH} (MAX)	3	5.5	7	pF
V_{HYST}	Hysteresis for Schmitt Trigger Inputs[5]	V_{CCIO} = 3.3 V, Hysteresis = Large	—	450	—	mV
		V_{CCIO} = 2.5 V, Hysteresis = Large	—	250	—	mV
		V_{CCIO} = 1.8 V, Hysteresis = Large	—	125	—	mV
		V_{CCIO} = 1.5 V, Hysteresis = Large	—	100	—	mV
		V_{CCIO} = 3.3 V, Hysteresis = Small	—	250	—	mV
		V_{CCIO} = 2.5 V, Hysteresis = Small	—	150	—	mV
		V_{CCIO} = 1.8 V, Hysteresis = Small	—	60	—	mV
		V_{CCIO} = 1.5 V, Hysteresis = Small	—	40	—	mV

1. Input or I/O leakage current is measured with the pin configured as an input or as an I/O with the output driver tri-stated. It is not measured with the output driver active. Bus maintenance circuits are disabled.
2. T_A 25 °C, f = 1.0 MHz.
3. Please refer to V_{IL} and V_{IH} in the sysIO Single-Ended DC Electrical Characteristics table of this document.
4. When V_{IH} is higher than V_{CCIO}, a transient current typically of 30 ns in duration or less with a peak current of 6 mA can occur on the high-to-low transition. For true LVDS output pins in MachXO2-640U, MachXO2-1200/U and larger devices, V_{IH} must be less than or equal to V_{CCIO}.
5. With bus keeper circuit turned on. For more details, refer to TN1202, MachXO2 sysIO Usage Guide.

Programming and Erase Flash Supply Current – ZE Devices[1, 2, 3, 4]

Symbol	Parameter	Device	Typ.[5]	Units
I_{CC}	Core Power Supply	LCMXO2-256ZE	13	mA
		LCMXO2-640ZE	14	mA
		LCMXO2-1200ZE	15	mA
		LCMXO2-2000ZE	17	mA
		LCMXO2-4000ZE	18	mA
		LCMXO2-7000ZE	20	mA
I_{CCIO}	Bank Power Supply[6]	All devices	0	mA

1. For further information on supply current, please refer to TN1198, Power Estimation and Management for MachXO2 Devices.
2. Assumes all inputs are held at V_{CCIO} or GND and all outputs are tri-stated.
3. Typical user pattern.
4. JTAG programming is at 25 MHz.
5. TJ = 25 °C, power supplies at nominal voltage.
6. Per bank. V_{CCIO} = 2.5 V. Does not include pull-up/pull-down.

sysIO Recommended Operating Conditions

Standard	V_{CCIO} (V)			V_{REF} (V)		
	Min.	Typ.	Max.	Min.	Typ.	Max.
LVCMOS 3.3	3.135	3.3	3.6	—	—	—
LVCMOS 2.5	2.375	2.5	2.625	—	—	—
LVCMOS 1.8	1.71	1.8	1.89	—	—	—
LVCMOS 1.5	1.425	1.5	1.575	—	—	—
LVCMOS 1.2	1.14	1.2	1.26	—	—	—
LVTTL	3.135	3.3	3.6	—	—	—
PCI[3]	3.135	3.3	3.6	—	—	—
SSTL25	2.375	2.5	2.625	1.15	1.25	1.35
SSTL18	1.71	1.8	1.89	0.833	0.9	0.969
HSTL18	1.71	1.8	1.89	0.816	0.9	1.08
LVCMOS25R33	3.135	3.3	3.6	1.1	1.25	1.4
LVCMOS18R33	3.135	3.3	3.6	0.75	0.9	1.05
LVCMOS18R25	2.375	2.5	2.625	0.75	0.9	1.05
LVCMOS15R33	3.135	3.3	3.6	0.6	0.75	0.9
LVCMOS15R25	2.375	2.5	2.625	0.6	0.75	0.9
LVCMOS12R33[4]	3.135	3.3	3.6	0.45	0.6	0.75
LVCMOS12R25[4]	2.375	2.5	2.625	0.45	0.6	0.75
LVCMOS10R33[4]	3.135	3.3	3.6	0.35	0.5	0.65
LVCMOS10R25[4]	2.375	2.5	2.625	0.35	0.5	0.65
LVDS25[1, 2]	2.375	2.5	2.625	—	—	—
LVDS33[1, 2]	3.135	3.3	3.6	—	—	—
LVPECL[1]	3.135	3.3	3.6	—	—	—
BLVDS[1]	2.375	2.5	2.625	—	—	—
RSDS[1]	2.375	2.5	2.625	—	—	—
SSTL18D	1.71	1.8	1.89	—	—	—
SSTL25D	2.375	2.5	2.625	—	—	—
HSTL18D	1.71	1.8	1.89	—	—	—

1. Inputs on-chip. Outputs are implemented with the addition of external resistors.
2. MachXO2-640U, MachXO2-1200/U and larger devices have dedicated LVDS buffers.
3. Input on the bottom bank of the MachXO2-640U, MachXO2-1200/U and larger devices only.
4. Supported only for inputs and BIDIs for all ZE devices, and –6 speed grade for HE and HC devices.

Parameter	Description	Device	–6		–5		–4		Units
			Min.	Max.	Min.	Max.	Min.	Max.	
LPDDR[9, 12]									
t_{DVADQ}	Input Data Valid After DQS Input	MachXO2-1200/U and larger devices, right side only.[13]	—	0.369	—	0.395	—	0.421	UI
t_{DVEDQ}	Input Data Hold After DQS Input		0.529	—	0.530	—	0.527	—	UI
t_{DQVBS}	Output Data Invalid Before DQS Output		0.25	—	0.25	—	0.25	—	UI
t_{DQVAS}	Output Data Invalid After DQS Output		0.25	—	0.25	—	0.25	—	UI
f_{DATA}	MEM LPDDR Serial Data Speed		—	280	—	250	—	208	Mbps
f_{SCLK}	SCLK Frequency		—	140	—	125	—	104	MHz
f_{LPDDR}	LPDDR Data Transfer Rate		0	280	0	250	0	208	Mbps
DDR[9, 12]									
t_{DVADQ}	Input Data Valid After DQS Input	MachXO2-1200/U and larger devices, right side only.[13]	—	0.350	—	0.387	—	0.414	UI
t_{DVEDQ}	Input Data Hold After DQS Input		0.545	—	0.538	—	0.532	—	UI
t_{DQVBS}	Output Data Invalid Before DQS Output		0.25	—	0.25	—	0.25	—	UI
t_{DQVAS}	Output Data Invalid After DQS Output		0.25	—	0.25	—	0.25	—	UI
f_{DATA}	MEM DDR Serial Data Speed		—	300	—	250	—	208	Mbps
f_{SCLK}	SCLK Frequency		—	150	—	125	—	104	MHz
f_{MEM_DDR}	MEM DDR Data Transfer Rate		N/A	300	N/A	250	N/A	208	Mbps
DDR2[9, 12]									
t_{DVADQ}	Input Data Valid After DQS Input	MachXO2-1200/U and larger devices, right side only.[13]	—	0.360	—	0.378	—	0.406	UI
t_{DVEDQ}	Input Data Hold After DQS Input		0.555	—	0.549	—	0.542	—	UI
t_{DQVBS}	Output Data Invalid Before DQS Output		0.25	—	0.25	—	0.25	—	UI
t_{DQVAS}	Output Data Invalid After DQS Output		0.25	—	0.25	—	0.25	—	UI
f_{DATA}	MEM DDR Serial Data Speed		—	300	—	250	—	208	Mbps
f_{SCLK}	SCLK Frequency		—	150	—	125	—	104	MHz
f_{MEM_DDR2}	MEM DDR2 Data Transfer Rate		N/A	300	N/A	250	N/A	208	Mbps

1. Exact performance may vary with device and design implementation. Commercial timing numbers are shown at 85 °C and 1.14 V. Other operating conditions, including industrial, can be extracted from the Diamond software.
2. General I/O timing numbers based on LVCMOS 2.5, 8 mA, 0pf load, fast slew rate.
3. Generic DDR timing numbers based on LVDS I/O (for input, output, and clock ports).
4. DDR timing numbers based on SSTL25. DDR2 timing numbers based on SSTL18. LPDDR timing numbers based in LVCMOS18.
5. 7:1 LVDS (GDDR71) uses the LVDS I/O standard (for input, output, and clock ports).
6. For Generic DDRX1 mode $t_{SU} = t_{HO} = (t_{DVE} - t_{DVA} - 0.03\text{ ns})/2$.
7. The t_{SU_DEL} and t_{H_DEL} values use the SCLK_ZERHOLD default step size. Each step is 105 ps (–6), 113 ps (–5), 120 ps (–4).
8. This number for general purpose usage. Duty cycle tolerance is +/– 10%.
9. Duty cycle is +/–5% for system usage.
10. The above timing numbers are generated using the Diamond design tool. Exact performance may vary with the device selected.
11. High-speed DDR and LVDS not supported in SG32 (32 QFN) packages.
12. Advance information for MachXO2 devices in 48 QFN packages.
13. DDR memory interface not supported in QN84 (84 QFN) and SG32 (32 QFN) packages.

Parameter	Description	Device	–3		–2		–1		Units
			Min.	Max.	Min.	Max.	Min.	Max.	
Generic DDR4 Inputs with Clock and Data Centered at Pin Using PCLK Pin for Clock Input – GDDRX4_RX.ECLK.Centered[9, 12]									
t_{SU}	Input Data Setup Before ECLK	MachXO2-640U, MachXO2-1200/U and larger devices, bottom side only[11]	0.434	—	0.535	—	0.630	—	ns
t_{HO}	Input Data Hold After ECLK		0.385	—	0.395	—	0.463	—	ns
f_{DATA}	DDRX4 Serial Input Data Speed		—	420	—	352	—	292	Mbps
f_{DDRX4}	DDRX4 ECLK Frequency		—	210	—	176	—	146	MHz
f_{SCLK}	SCLK Frequency		—	53	—	44	—	37	MHz
7:1 LVDS Inputs – GDDR71_RX.ECLK.7.1[9, 12]									
t_{DVA}	Input Data Valid After ECLK	MachXO2-640U, MachXO2-1200/U and larger devices, bottom side only[11]	—	0.307	—	0.316	—	0.326	UI
t_{DVE}	Input Data Hold After ECLK		0.662	—	0.650	—	0.649	—	UI
f_{DATA}	DDR71 Serial Input Data Speed		—	420	—	352	—	292	Mbps
f_{DDR71}	DDR71 ECLK Frequency		—	210	—	176	—	146	MHz
f_{CLKIN}	7:1 Input Clock Frequency (SCLK) (minimum limited by PLL)		—	60	—	50	—	42	MHz
Generic DDR Outputs with Clock and Data Aligned at Pin Using PCLK Pin for Clock Input – GDDRX1_TX.SCLK.Aligned[9, 12]									
t_{DIA}	Output Data Invalid After CLK Output	All MachXO2 devices, all sides	—	0.850	—	0.910	—	0.970	ns
t_{DIB}	Output Data Invalid Before CLK Output		—	0.850	—	0.910	—	0.970	ns
f_{DATA}	DDRX1 Output Data Speed		—	140	—	116	—	98	Mbps
f_{DDRX1}	DDRX1 SCLK frequency		—	70	—	58	—	49	MHz
Generic DDR Outputs with Clock and Data Centered at Pin Using PCLK Pin for Clock Input – GDDRX1_TX.SCLK.Centered[9, 12]									
t_{DVB}	Output Data Valid Before CLK Output	All MachXO2 devices, all sides	2.720	—	3.380	—	4.140	—	ns
t_{DVA}	Output Data Valid After CLK Output		2.720	—	3.380	—	4.140	—	ns
f_{DATA}	DDRX1 Output Data Speed		—	140	—	116	—	98	Mbps
f_{DDRX1}	DDRX1 SCLK Frequency (minimum limited by PLL)		—	70	—	58	—	49	MHz
Generic DDRX2 Outputs with Clock and Data Aligned at Pin Using PCLK Pin for Clock Input – GDDRX2_TX.ECLK.Aligned[9, 12]									
t_{DIA}	Output Data Invalid After CLK Output	MachXO2-640U, MachXO2-1200/U and larger devices, top side only	—	0.270	—	0.300	—	0.330	ns
t_{DIB}	Output Data Invalid Before CLK Output		—	0.270	—	0.300	—	0.330	ns
f_{DATA}	DDRX2 Serial Output Data Speed		—	280	—	234	—	194	Mbps
f_{DDRX2}	DDRX2 ECLK frequency		—	140	—	117	—	97	MHz
f_{SCLK}	SCLK Frequency		—	70	—	59	—	49	MHz

MachXO2 Family Data Sheet
Ordering Information

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MachXO2 Part Number Description

LCMXO2 – XXXX X X X – X XXXXXX X XX XX

Device Family
MachXO2 PLD

Logic Capacity
256 = 256 LUTs
640 = 640 LUTs
1200 = 1280 LUTs
2000 = 2112 LUTs
4000 = 4320 LUTs
7000 = 6864 LUTs

I/O Count
Blank = Standard Device
U = Ultra High I/O Device

Power/Performance
Z = Low Power
H = High Performance

Supply Voltage
C = 2.5 V / 3.3 V
E = 1.2 V

Speed
1 = Slowest
2
3 = Fastest
} Low Power

4 = Slowest
5
6 = Fastest
} High Performance

Device Status
Blank = Production Device
ES = Engineering Sample
R1 = Production Release 1 Device
1K = WLCSP Package, 1,000 parts per reel

Shipping Method
Blank = Trays
TR = Tape and Reel

Grade
C = Commercial
I = Industrial

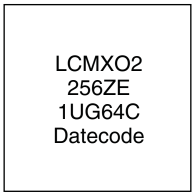
Package

UWG25 = 25-Ball Halogen-Free WLCSP (0.4 mm Pitch)
SG32 = 32-Pin Halogen-Free QFN (0.5 mm Pitch)
SG48 = 48-Pin Halogen-Free QFN (0.5 mm Pitch)
UWG49 = 49-ball Halogen-Free WLCSP (0.4 mm Pitch)
UMG64 = 64-Ball Halogen-Free ucBGA (0.4 mm Pitch)
QN84 = 84-Pin Halogen-Free QFN (0.5 mm Pitch)
TG100 = 100-Pin Halogen-Free TQFP
TG144 = 144-Pin Halogen-Free TQFP
MG132 = 132-Ball Halogen-Free csBGA (0.5 mm Pitch)
MG184 = 184-Ball Halogen-Free csBGA (0.5 mm Pitch)
BG256 = 256-Ball Halogen-Free caBGA (0.8 mm Pitch)
FTG256 = 256-Ball Halogen-Free ftBGA (1.0 mm Pitch)
BG332 = 332-Ball Halogen-Free caBGA (0.8 mm Pitch)
FG484 = 484-Ball Halogen-Free fpBGA (1.0 mm Pitch)

* 48-pin QFN information is 'Advanced'.

Ordering Information

MachXO2 devices have top-side markings, for commercial and industrial grades, as shown below:



Notes:

1. Markings are abbreviated for small packages.

2. See PCN 05A-12 for information regarding a change to the top-side mark logo.

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-7000ZE-1TG144C	6864	1.2 V	–1	Halogen-Free TQFP	144	COM
LCMXO2-7000ZE-2TG144C	6864	1.2 V	–2	Halogen-Free TQFP	144	COM
LCMXO2-7000ZE-3TG144C	6864	1.2 V	–3	Halogen-Free TQFP	144	COM
LCMXO2-7000ZE-1BG256C	6864	1.2 V	–1	Halogen-Free caBGA	256	COM
LCMXO2-7000ZE-2BG256C	6864	1.2 V	–2	Halogen-Free caBGA	256	COM
LCMXO2-7000ZE-3BG256C	6864	1.2 V	–3	Halogen-Free caBGA	256	COM
LCMXO2-7000ZE-1FTG256C	6864	1.2 V	–1	Halogen-Free ftBGA	256	COM
LCMXO2-7000ZE-2FTG256C	6864	1.2 V	–2	Halogen-Free ftBGA	256	COM
LCMXO2-7000ZE-3FTG256C	6864	1.2 V	–3	Halogen-Free ftBGA	256	COM
LCMXO2-7000ZE-1BG332C	6864	1.2 V	–1	Halogen-Free caBGA	332	COM
LCMXO2-7000ZE-2BG332C	6864	1.2 V	–2	Halogen-Free caBGA	332	COM
LCMXO2-7000ZE-3BG332C	6864	1.2 V	–3	Halogen-Free caBGA	332	COM
LCMXO2-7000ZE-1FG484C	6864	1.2 V	–1	Halogen-Free fpBGA	484	COM
LCMXO2-7000ZE-2FG484C	6864	1.2 V	–2	Halogen-Free fpBGA	484	COM
LCMXO2-7000ZE-3FG484C	6864	1.2 V	–3	Halogen-Free fpBGA	484	COM

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-1200ZE-1TG100CR1[1]	1280	1.2 V	–1	Halogen-Free TQFP	100	COM
LCMXO2-1200ZE-2TG100CR1[1]	1280	1.2 V	–2	Halogen-Free TQFP	100	COM
LCMXO2-1200ZE-3TG100CR1[1]	1280	1.2 V	–3	Halogen-Free TQFP	100	COM
LCMXO2-1200ZE-1MG132CR1[1]	1280	1.2 V	–1	Halogen-Free csBGA	132	COM
LCMXO2-1200ZE-2MG132CR1[1]	1280	1.2 V	–2	Halogen-Free csBGA	132	COM
LCMXO2-1200ZE-3MG132CR1[1]	1280	1.2 V	–3	Halogen-Free csBGA	132	COM
LCMXO2-1200ZE-1TG144CR1[1]	1280	1.2 V	–1	Halogen-Free TQFP	144	COM
LCMXO2-1200ZE-2TG144CR1[1]	1280	1.2 V	–2	Halogen-Free TQFP	144	COM
LCMXO2-1200ZE-3TG144CR1[1]	1280	1.2 V	–3	Halogen-Free TQFP	144	COM

1. Specifications for the “LCMXO2-1200ZE-speed package CR1” are the same as the “LCMXO2-1200ZE-speed package C” devices respectively, except as specified in the R1 Device Specifications section of this data sheet.

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-2000UHC-4FG484C	2112	2.5 V / 3.3 V	–4	Halogen-Free fpBGA	484	COM
LCMXO2-2000UHC-5FG484C	2112	2.5 V / 3.3 V	–5	Halogen-Free fpBGA	484	COM
LCMXO2-2000UHC-6FG484C	2112	2.5 V / 3.3 V	–6	Halogen-Free fpBGA	484	COM

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-4000HC-4QN84C	4320	2.5 V / 3.3 V	–4	Halogen-Free QFN	84	COM
LCMXO2-4000HC-5QN84C	4320	2.5 V / 3.3 V	–5	Halogen-Free QFN	84	COM
LCMXO2-4000HC-6QN84C	4320	2.5 V / 3.3 V	–6	Halogen-Free QFN	84	COM
LCMXO2-4000HC-4MG132C	4320	2.5 V / 3.3 V	–4	Halogen-Free csBGA	132	COM
LCMXO2-4000HC-5MG132C	4320	2.5 V / 3.3 V	–5	Halogen-Free csBGA	132	COM
LCMXO2-4000HC-6MG132C	4320	2.5 V / 3.3 V	–6	Halogen-Free csBGA	132	COM
LCMXO2-4000HC-4TG144C	4320	2.5 V / 3.3 V	–4	Halogen-Free TQFP	144	COM
LCMXO2-4000HC-5TG144C	4320	2.5 V / 3.3 V	–5	Halogen-Free TQFP	144	COM
LCMXO2-4000HC-6TG144C	4320	2.5 V / 3.3 V	–6	Halogen-Free TQFP	144	COM
LCMXO2-4000HC-4BG256C	4320	2.5 V / 3.3 V	–4	Halogen-Free caBGA	256	COM
LCMXO2-4000HC-5BG256C	4320	2.5 V / 3.3 V	–5	Halogen-Free caBGA	256	COM
LCMXO2-4000HC-6BG256C	4320	2.5 V / 3.3 V	–6	Halogen-Free caBGA	256	COM
LCMXO2-4000HC-4FTG256C	4320	2.5 V / 3.3 V	–4	Halogen-Free ftBGA	256	COM
LCMXO2-4000HC-5FTG256C	4320	2.5 V / 3.3 V	–5	Halogen-Free ftBGA	256	COM
LCMXO2-4000HC-6FTG256C	4320	2.5 V / 3.3 V	–6	Halogen-Free ftBGA	256	COM
LCMXO2-4000HC-4BG332C	4320	2.5 V / 3.3 V	–4	Halogen-Free caBGA	332	COM
LCMXO2-4000HC-5BG332C	4320	2.5 V / 3.3 V	–5	Halogen-Free caBGA	332	COM
LCMXO2-4000HC-6BG332C	4320	2.5 V / 3.3 V	–6	Halogen-Free caBGA	332	COM
LCMXO2-4000HC-4FG484C	4320	2.5 V / 3.3 V	–4	Halogen-Free fpBGA	484	COM
LCMXO2-4000HC-5FG484C	4320	2.5 V / 3.3 V	–5	Halogen-Free fpBGA	484	COM
LCMXO2-4000HC-6FG484C	4320	2.5 V / 3.3 V	–6	Halogen-Free fpBGA	484	COM

MachXO2 Family Data Sheet Supplemental Information

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For Further Information

A variety of technical notes for the MachXO2 family are available on the Lattice web site.

- TN1198, Power Estimation and Management for MachXO2 Devices
- TN1199, MachXO2 sysCLOCK PLL Design and Usage Guide
- TN1201, Memory Usage Guide for MachXO2 Devices
- TN1202, MachXO2 sysIO Usage Guide
- TN1203, Implementing High-Speed Interfaces with MachXO2 Devices
- TN1204, MachXO2 Programming and Configuration Usage Guide
- TN1205, Using User Flash Memory and Hardened Control Functions in MachXO2 Devices
- TN1206, MachXO2 SRAM CRC Error Detection Usage Guide
- TN1207, Using TraceID in MachXO2 Devices
- TN1074, PCB Layout Recommendations for BGA Packages
- TN1087, Minimizing System Interruption During Configuration Using TransFR Technology
- AN8086, Designing for Migration from MachXO2-1200-R1 to Standard (non-R1) Devices
- AN8066, Boundary Scan Testability with Lattice sysIO Capability

- MachXO2 Device Pinout Files
- Thermal Management document
- Lattice design tools

For further information on interface standards, refer to the following web sites:

- JEDEC Standards (LVTTL, LVCMOS, LVDS, DDR, DDR2, LPDDR): www.jedec.org
- PCI: www.pcisig.com